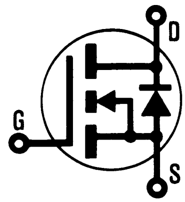
Data Sheet No. PD-9.407

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS IRFJ420 IRFJ421 IRFJ422 IRFJ423

N-CHANNEL POWER MOSFETs



500 Volt, 3.0 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

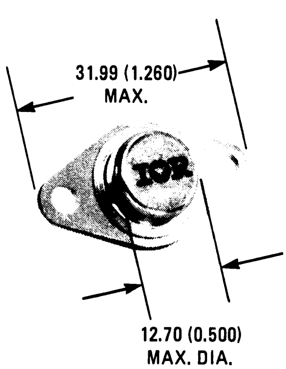
Features:

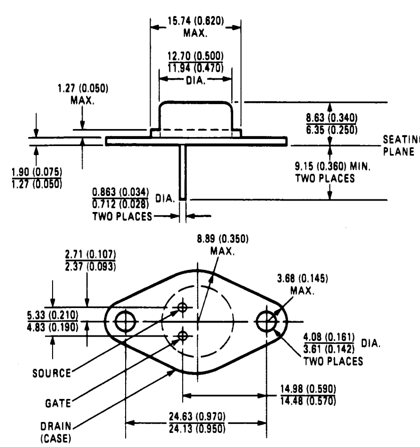
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ420	500V	3.0Ω	2.5A
IRFJ421	450V	3.0Ω	2.5A
IRFJ422	500V	4.0Ω	2.0A
IRFJ423	450V	4.0Ω	2.0A

CASE STYLE AND DIMENSIONS



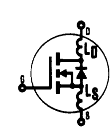


Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

Absolute Maximum Ratings

	Parameter	IRFJ420	IRFJ421	IRFJ422	IRFJ423	Units
V_{DS}	Drain - Source Voltage ①	500	450	500	450	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	500	450	500	450	V
I_D @ T_C = 25°C	Continuous Drain Current	2.5	2.5	2.0	2.0	A
I_D @ T_C = 100°C	Continuous Drain Current	1.5	1.5	1.0	1.0	A
I_{DM}	Pulsed Drain Current ③	10	10	8.0	8.0	A
V_{GS}	Gate - Source Voltage	± 20				V
P_D @ T_C = 25°C	Max. Power Dissipation	40 (See Fig. 14)				W
	Linear Derating Factor	0.32 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 10	10	8.0	8.0	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

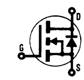
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

	Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ420 IRFJ422	500	–	–	V	V_{GS} = 0V
		IRFJ421 IRFJ423	450	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ420 IRFJ421	2.5	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ422 IRFJ423	2.0	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ420 IRFJ421	–	2.5	3.0	Ω	V_{GS} = 10V, I_D = 1.0A
		IRFJ422 IRFJ423	–	3.0	4.0	Ω	
g_{fs}	Forward Transconductance ②	ALL	1.0	1.75	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 1.0A
C_{iss}	Input Capacitance	ALL	–	300	400	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	75	150	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	20	40	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	30	60	ns	V_{DD} ≈ 0.5 BV_{DSS}, I_D = 1.0A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	25	50	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	30	60	ns	
t_f	Fall Time	ALL	–	15	30	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	11	15	nC	V_{GS} = 10V, I_D = 3.0A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	5.0	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	6.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. / Modified MOSFET symbol showing the internal device inductances. 
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	3.1	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ420 IRFJ421	–	–	2.5	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ422 IRFJ423	–	–	2.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ420 IRFJ421	–	–	10	A	
		IRFJ422 IRFJ423	–	–	8.0	A	
V_{SD}	Diode Forward Voltage ②	IRFJ420 IRFJ421	–	–	1.4	V	$T_C = 25°C, I_S = 2.5A, V_{GS} = 0V$
		IRFJ422 IRFJ423	–	–	1.3	V	$T_C = 25°C, I_S = 2.0A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	ALL	–	600	–	ns	$T_J = 150°C, I_F = 2.5A, dI_F/dt = 100A/\mu s$
Q_{RR}	Reverse Recovered Charge	ALL	–	3.5	–	μC	$T_J = 150°C, I_F = 2.5A, dI_F/dt = 100A/\mu s$
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① $T_J = 25°C$ to $150°C$. ② Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

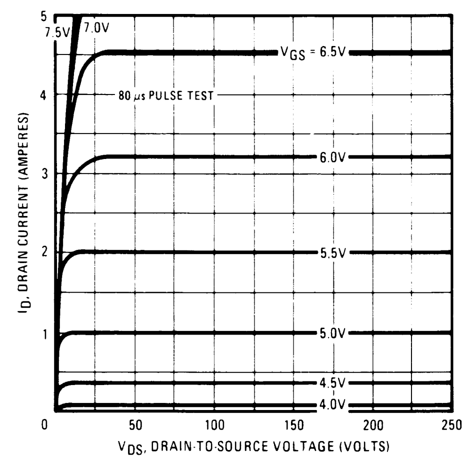


Fig. 1 – Typical Output Characteristics

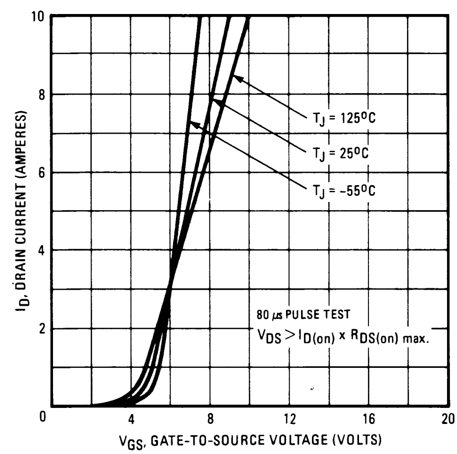


Fig. 2 – Typical Transfer Characteristics

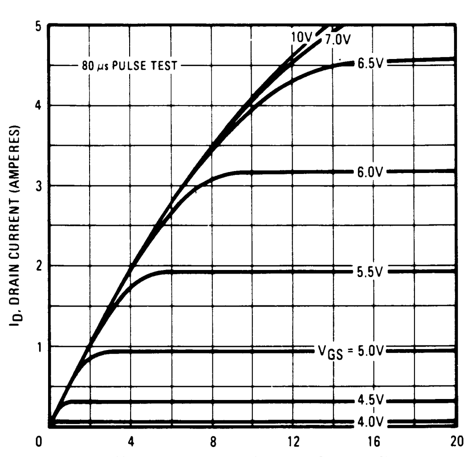


Fig. 3 – Typical Saturation Characteristics

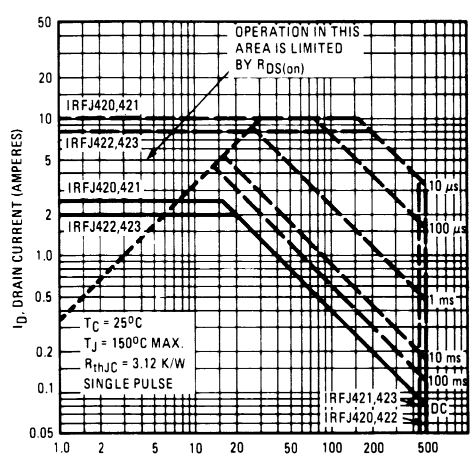


Fig. 4 – Maximum Safe Operating Area

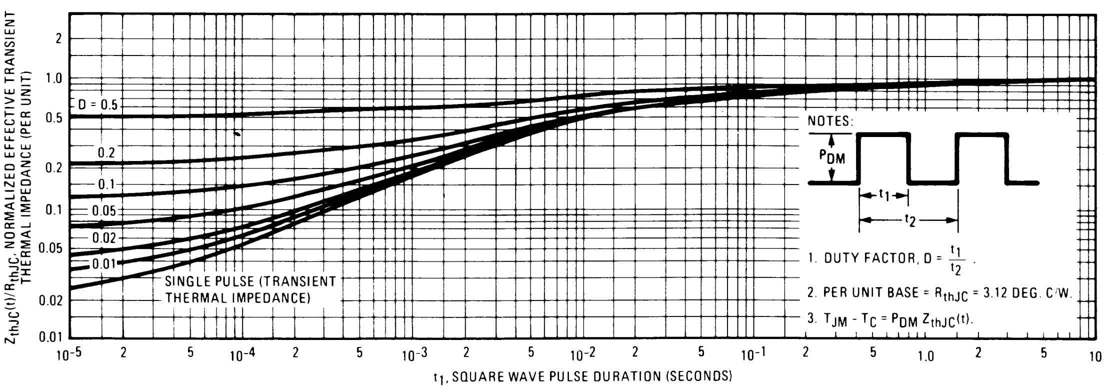


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

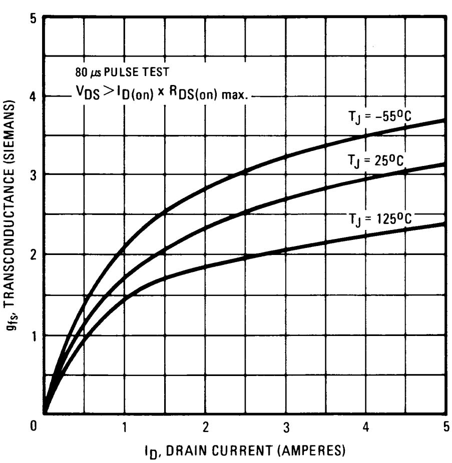


Fig. 6 – Typical Transconductance Vs. Drain Current

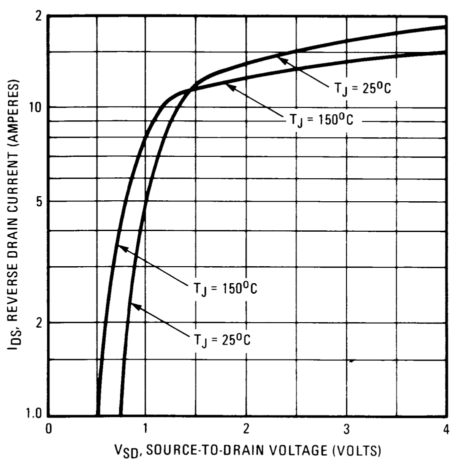


Fig. 7 – Typical Source-Drain Diode Forward Voltage

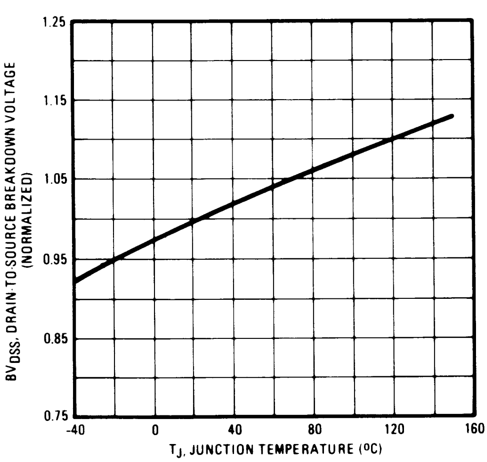


Fig. 8 – Breakdown Voltage Vs. Temperature

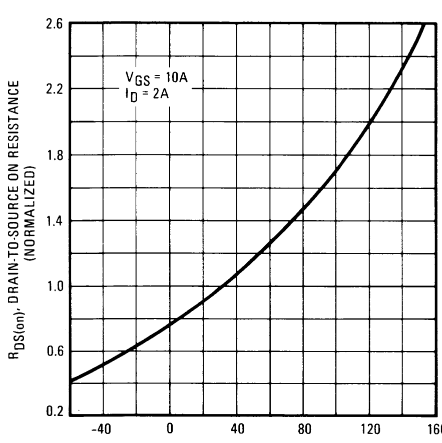


Fig. 9 – Normalized On-Resistance Vs. Temperature

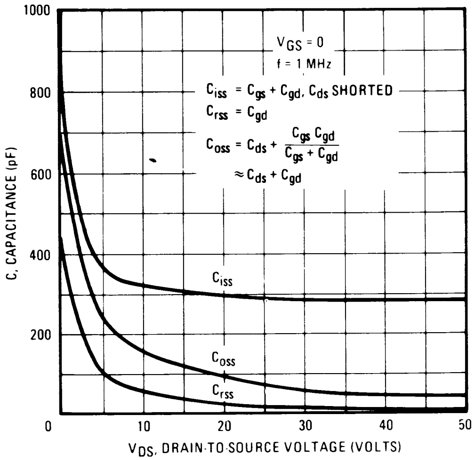


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

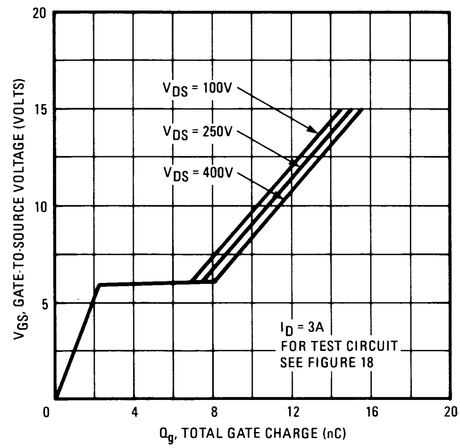


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

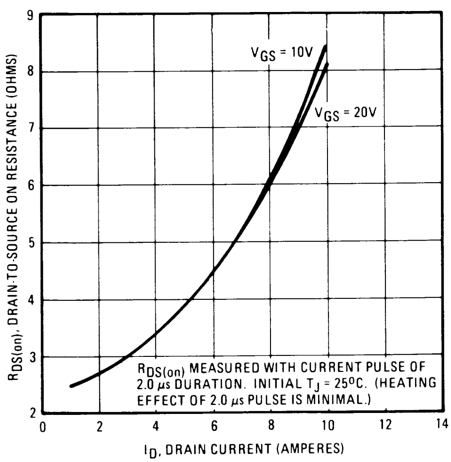


Fig. 12 — Typical On-Resistance Vs. Drain Current

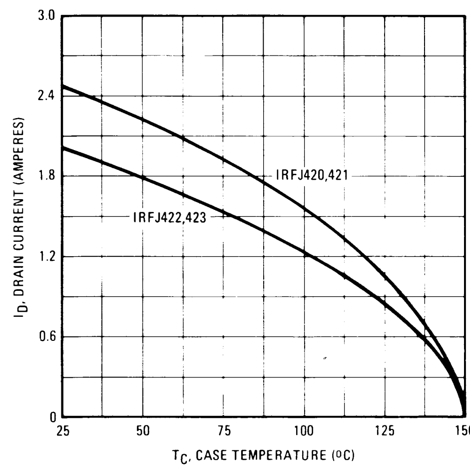


Fig. 13 — Maximum Drain Current Vs. Case Temperature

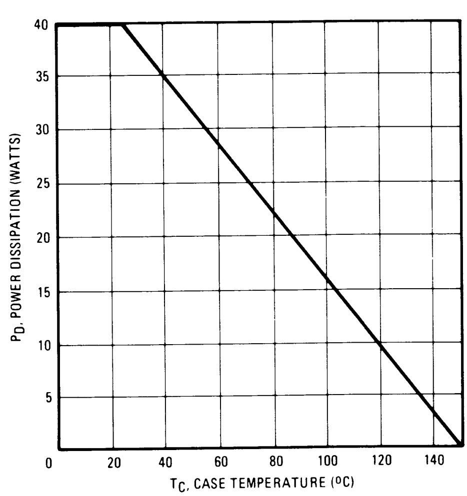


Fig. 14 — Power Vs. Temperature Derating Curve

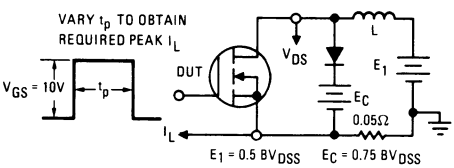


Fig. 15 — Clamped Inductive Test Circuit

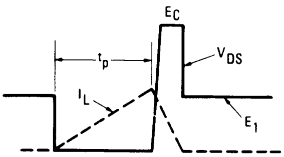


Fig. 16 — Clamped Inductive Waveforms

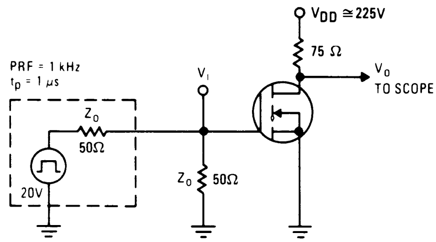


Fig. 17 — Switching Time Test Circuit

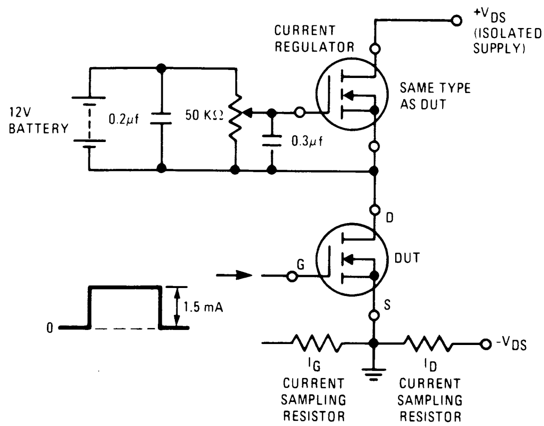


Fig. 18 — Gate Charge Test Circuit

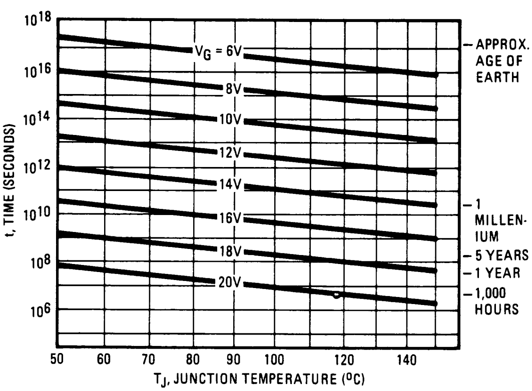


***Fig. 19 — Typical Time to Accumulated 1% Failure**

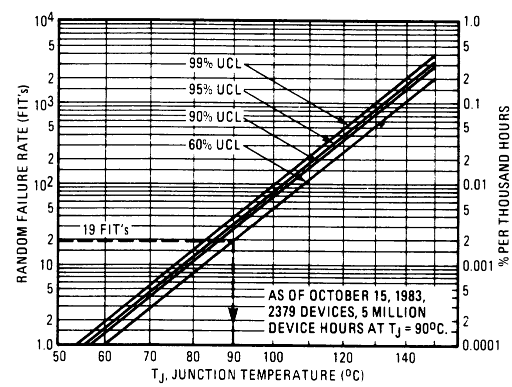


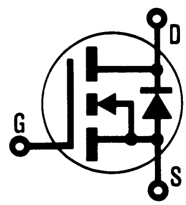
Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

N-CHANNEL POWER MOSFETs



IRFJ430 IRFJ431 IRFJ432 IRFJ433

500 Volt, 1.5 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

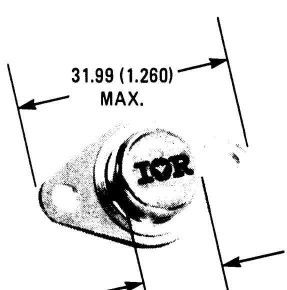
Features:

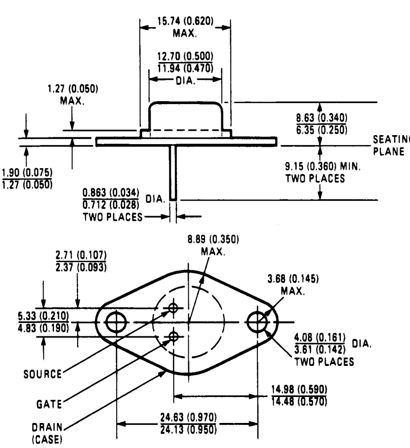
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ430	500V	1.5Ω	3.8A
IRFJ431	450V	1.5Ω	3.8A
IRFJ432	500V	2.0Ω	3.3A
IRFJ433	450V	2.0Ω	3.3A

CASE STYLE AND DIMENSIONS





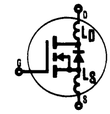
Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

Absolute Maximum Ratings

Parameter		IRFJ430	IRFJ431	IRFJ432	IRFJ433	Units
V_{DS}	Drain - Source Voltage ①	500	450	500	450	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20KΩ) ①	500	450	500	450	V
I_D @ T_C = 25°C	Continuous Drain Current	4.0	4.0	3.0	3.0	A
I_D @ T_C = 100°C	Continuous Drain Current	2.5	2.5	3.0	3.0	A
I_{DM}	Pulsed Drain Current ③	15	15	12	12	A
V_{GS}	Gate - Source Voltage	± 20				V
P_D @ T_C = 25°C	Max. Power Dissipation	50 (See Fig. 14)				W
	Linear Derating Factor	0.4 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 15	15	12	12	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

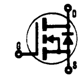
Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ430 IRFJ432	500	–	–	V	V_{GS} = 0V
		IRFJ431 IRFJ433	450	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ430 IRFJ431	4.0	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ432 IRFJ433	3.0	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ430 IRFJ431	–	1.3	1.5	Ω	V_{GS} = 10V, I_D = 2.1A
		IRFJ432 IRFJ433	–	1.5	2.0	Ω	
g_{fs}	Forward Transconductance ②	ALL	2.5	3	–	S (Ω)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 2.1A
C_{iss}	Input Capacitance	ALL	–	600	800	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	100	200	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	30	60	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	–	30	ns	V_{DD} = 225V, I_D = 2.1A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	–	30	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	–	55	ns	
t_f	Fall Time	ALL	–	–	30	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	22	30	nC	V_{GS} = 10V, I_D = 4.8A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	11	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	11	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. Modified MOSFET symbol showing the internal device inductances.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	2.5	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ430 IRFJ431	–	–	3.8	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ432 IRFJ433	–	–	2.4	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ430 IRFJ431	–	–	15	A	
		IRFJ432 IRFJ433	–	–	13	A	
V_{SD}	Diode Forward Voltage ②	IRFJ430 IRFJ431	–	–	1.4	V	T_C = 25°C, I_S = 3.8A, V_{GS} = 0V
		IRFJ432 IRFJ433	–	–	1.3	V	T_C = 25°C, I_S = 3.3A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	–	–	ns	T_J = 150°C, I_F = 3.8A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	–	–	μC	T_J = 150°C, I_F = 3.8A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

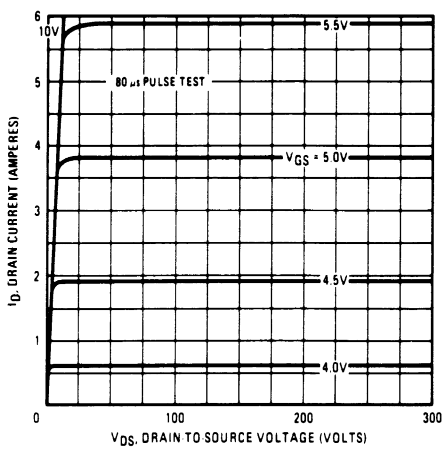


Fig. 1 — Typical Output Characteristics

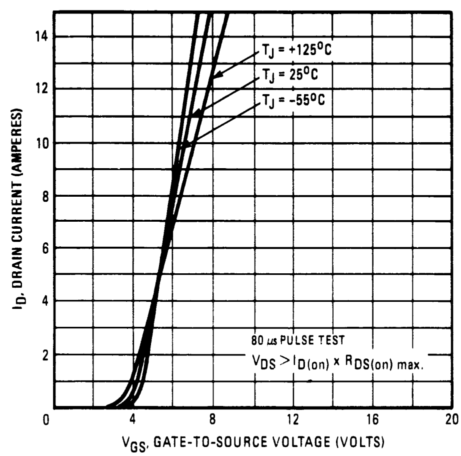


Fig. 2 — Typical Transfer Characteristics

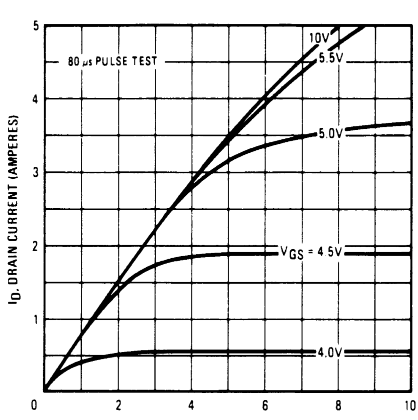


Fig. 3 — Typical Saturation Characteristics

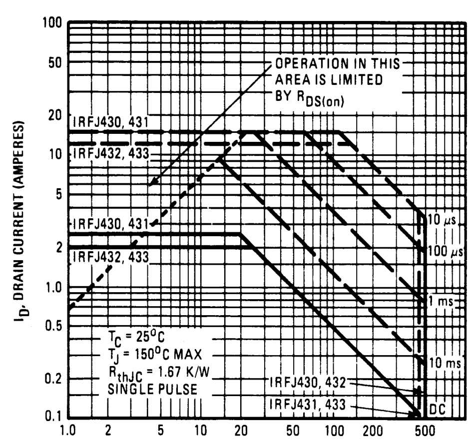


Fig. 4 — Maximum Safe Operating Area

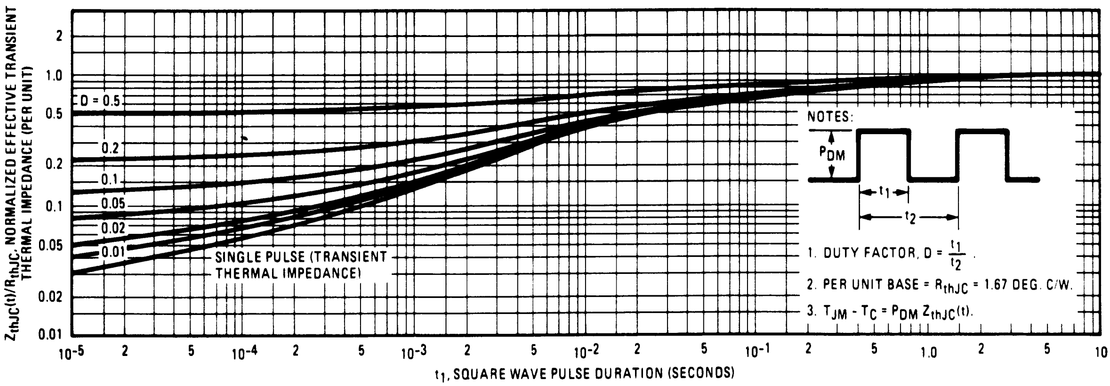


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

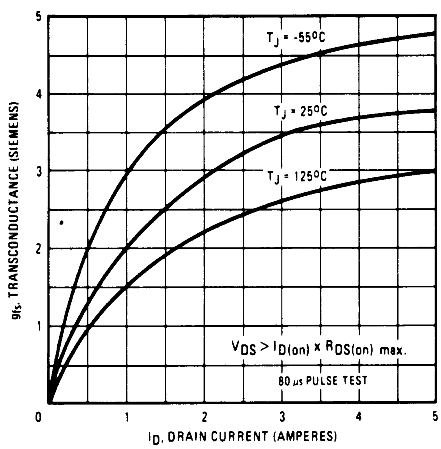


Fig. 6 — Typical Transconductance Vs. Drain Current

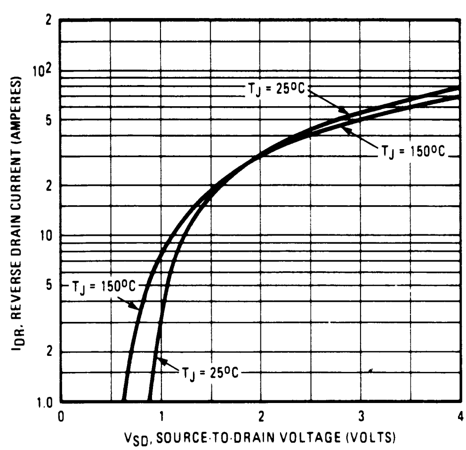


Fig. 7 — Typical Source-Drain Diode Forward Voltage

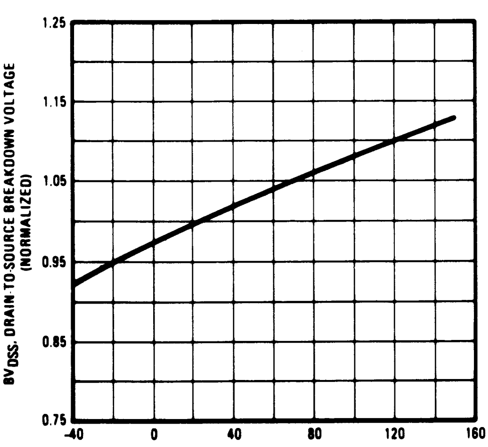


Fig. 8 — Breakdown Voltage Vs. Temperature

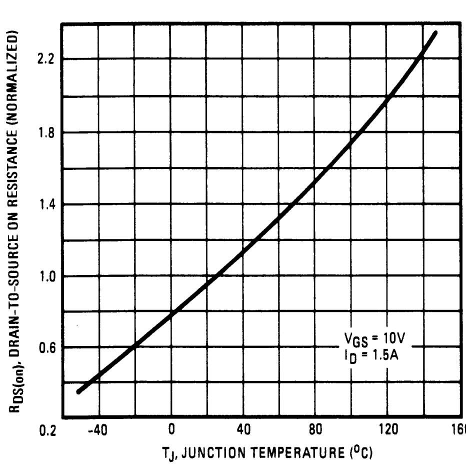


Fig. 9 — Normalized On-Resistance Vs. Temperature

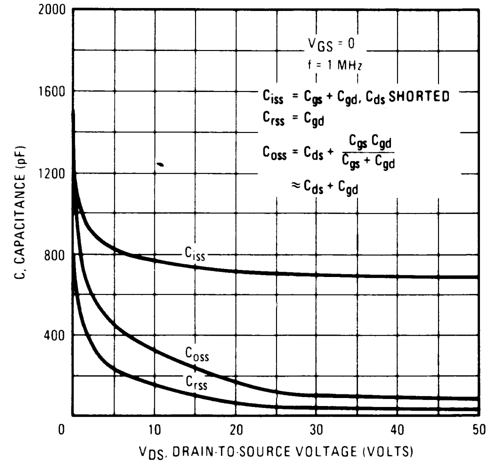


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

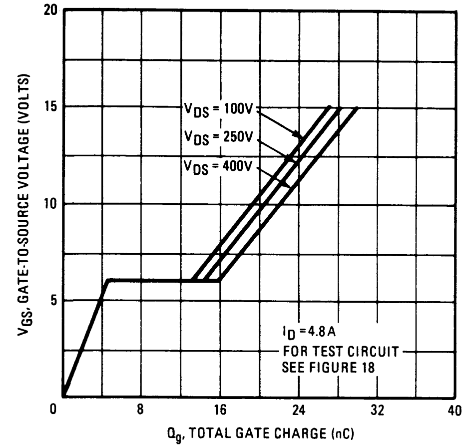


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

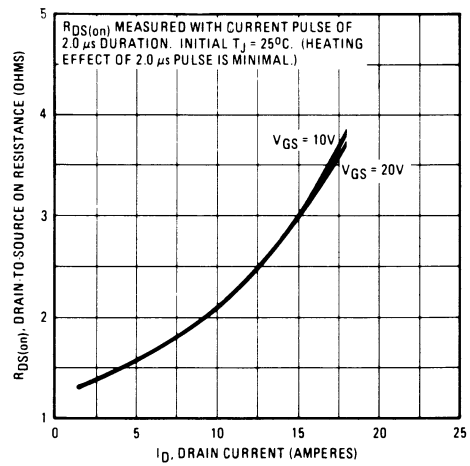


Fig. 12 — Typical On-Resistance Vs. Drain Current

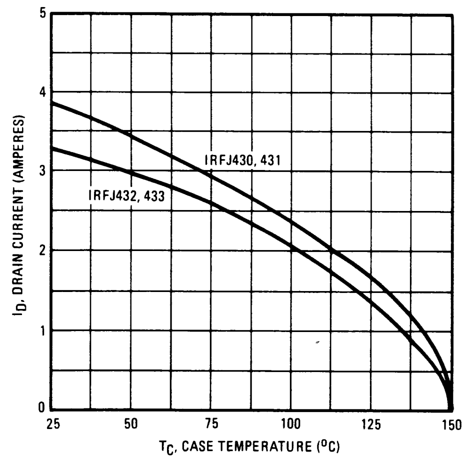


Fig. 13 — Maximum Drain Current Vs. Case Temperature

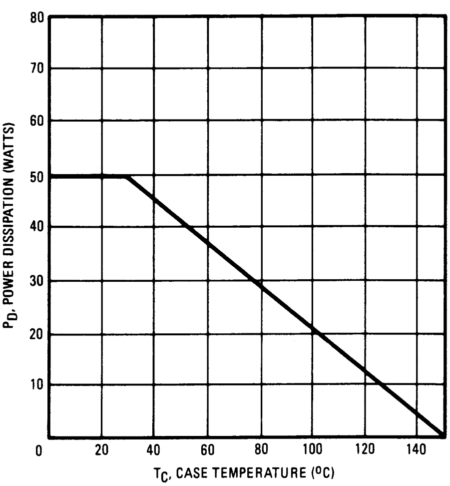


Fig. 14 — Power Vs. Temperature Derating Curve

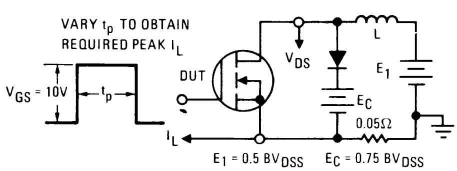


Fig. 15 — Clamped Inductive Test Circuit

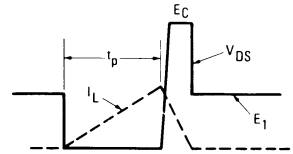


Fig. 16 — Clamped Inductive Waveforms

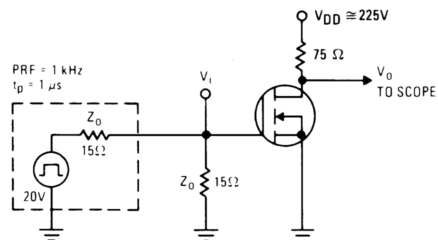


Fig. 17 — Switching Time Test Circuit

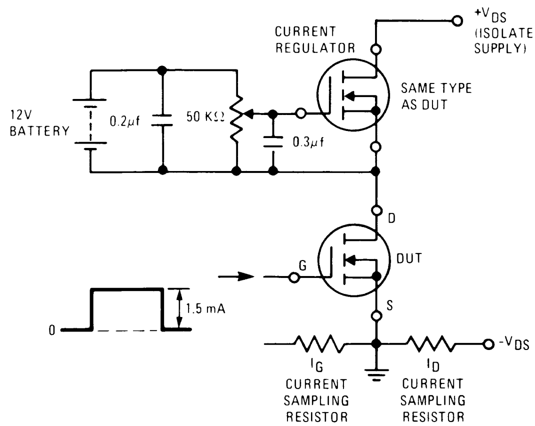


Fig. 18 — Gate Charge Test Circuit

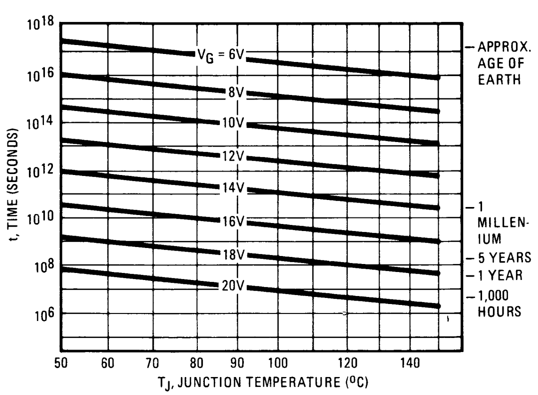


*Fig. 19 — Typical Time to Accumulated 1% Failure

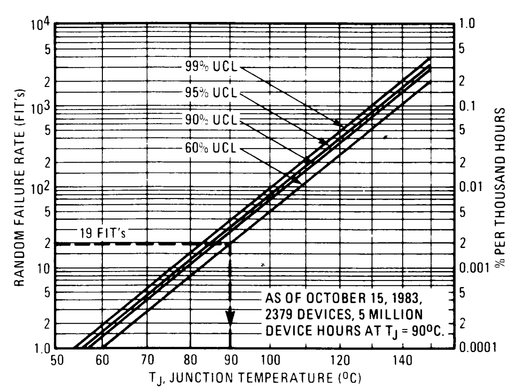


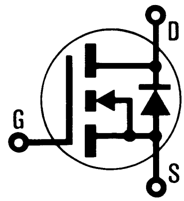
Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

N-CHANNEL POWER MOSFETs



IRFJ440 IRFJ441 IRFJ442 IRFJ443

500 Volt, 0.85 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

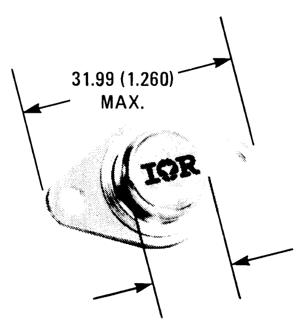
Features:

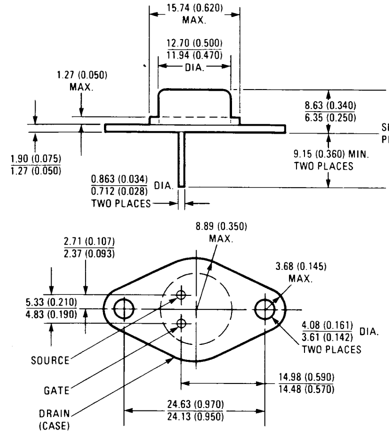
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ440	500V	0.85Ω	6.0A
IRFJ441	450V	0.85Ω	6.0A
IRFJ442	500V	1.10Ω	5.0A
IRFJ443	450V	1.10Ω	5.0A

CASE STYLE AND DIMENSIONS





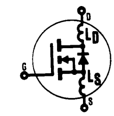
Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ440, IRFJ441, IRFJ442, IRFJ443 Devices

Absolute Maximum Ratings

Parameter		IRFJ440	IRFJ441	IRFJ442	IRFJ443	Units
V_{DS}	Drain - Source Voltage ①	500	450	500	450	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	500	450	500	450	V
I_D @ T_C = 25°C	Continuous Drain Current	6.0	6.0	5.0	5.0	A
I_D @ T_C = 100°C	Continuous Drain Current	4.0	4.0	3.0	3.0	A
I_{DM}	Pulsed Drain Current ③	24	24	20	20	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	70 (See Fig. 14)				W
	Linear Derating Factor	0.55 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 24	24	20	20	A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

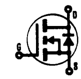
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions	
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ440 IRFJ442	500	–	–	V	V_{GS} = 0V	
		IRFJ441 IRFJ443	450	–	–	V	I_D = 250μA	
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA	
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V	
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V	
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V	
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C	
$I_{D(on)}$	On-State Drain Current ②	IRFJ440 IRFJ441	6.0	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V	
		IRFJ442 IRFJ443	5.0	–	–	A		
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ440 IRFJ441	–	0.8	0.85	Ω	V_{GS} = 10V, I_D = 3.3A	
		IRFJ442 IRFJ443	–	1.0	1.1	Ω		
g_{fs}	Forward Transconductance ②	ALL	4.0	6.5	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 3.3A	
C_{iss}	Input Capacitance	ALL	–	1225	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10	
C_{oss}	Output Capacitance	ALL	–	200	350	pF		
C_{rss}	Reverse Transfer Capacitance	ALL	–	85	150	pF		
$t_{d(on)}$	Turn-On Delay Time	ALL	–	17	35	ns	V_{DD} ≈ 200V, I_D = 3.3A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)	
t_r	Rise Time	ALL	–	5	15	ns		
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	42	90	ns		
t_f	Fall Time	ALL	–	14	30	ns		
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	42	60	nC	V_{GS} = 10V, I_D = 7.6A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)	
Q_{gs}	Gate-Source Charge	ALL	–	20	–	nC		
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	22	–	nC		
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.	Modified MOSFET symbol showing the internal device inductances.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.	

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.8	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ440 IRFJ441	–	–	6.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
		IRFJ442 IRFJ443	–	–	5.0	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ440 IRFJ441	–	–	24	A	
		IRFJ442 IRFJ443	–	–	20	A	
V_{SD}	Diode Forward Voltage ②	IRFJ440 IRFJ441	–	–	2.0	V	T_C = 25°C, I_S = 6.0A, V_{GS} = 0V
		IRFJ442 IRFJ443	–	–	1.9	V	T_C = 25°C, I_S = 5.2A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	1100	–	ns	T_J = 150°C, I_F = 6.0A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	6.4	–	μC	T_J = 150°C, I_F = 6.0A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

① T_J = 25°C to 150°C. ② Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

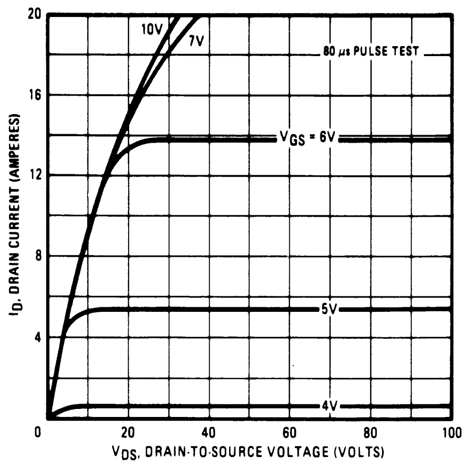


Fig. 1 – Typical Output Characteristics

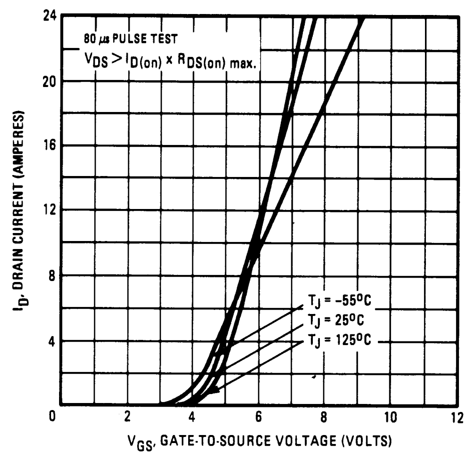


Fig. 2 – Typical Transfer Characteristics

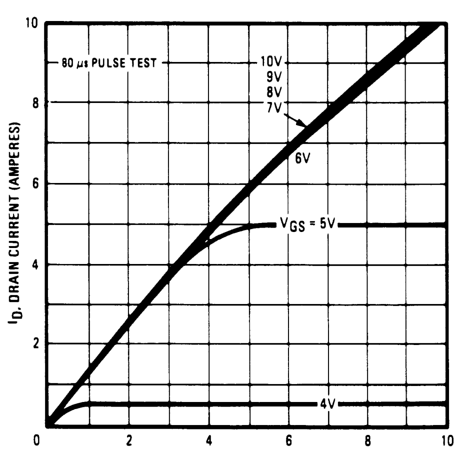


Fig. 3 – Typical Saturation Characteristics

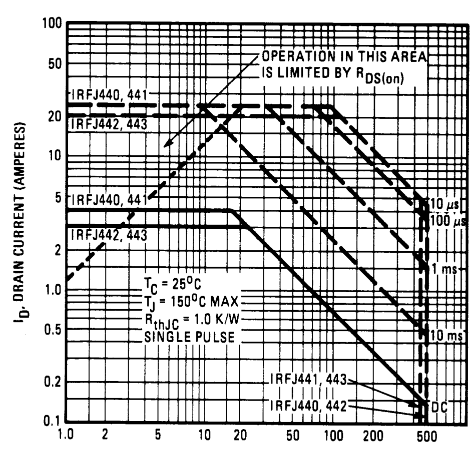


Fig. 4 – Maximum Safe Operating Area

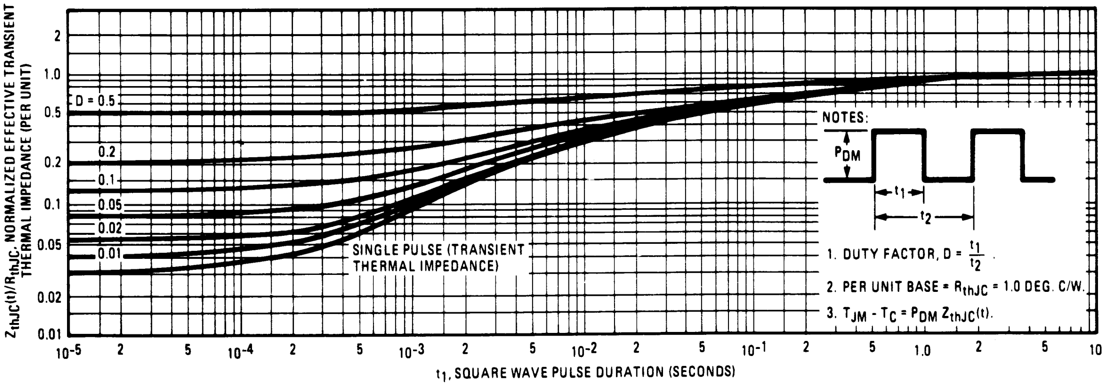


Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

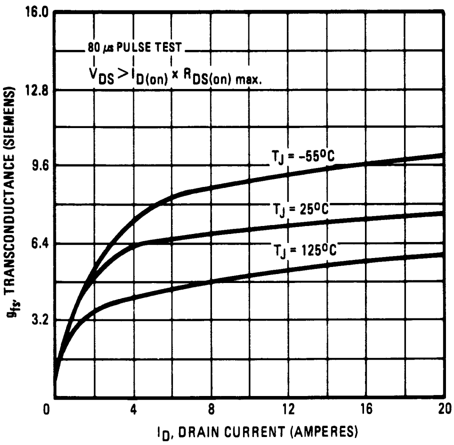


Fig. 6 — Typical Transconductance Vs. Drain Current

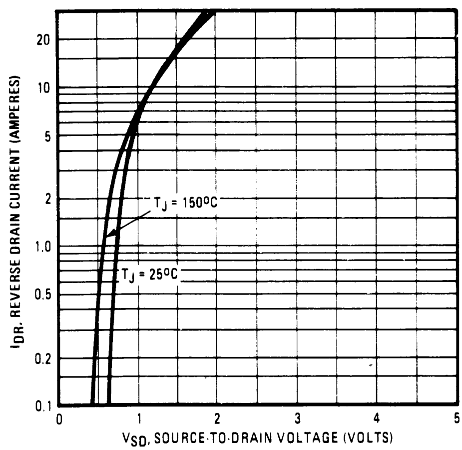


Fig. 7 — Typical Source-Drain Diode Forward Voltage

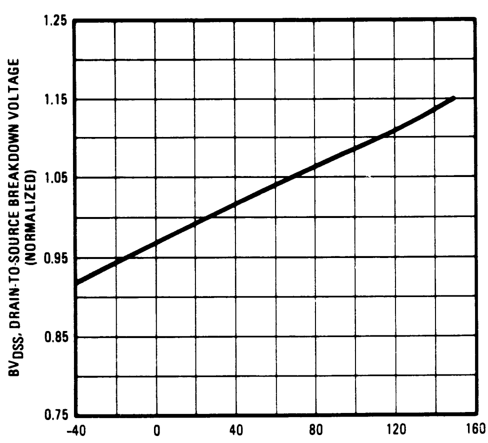


Fig. 8 — Breakdown Voltage Vs. Temperature

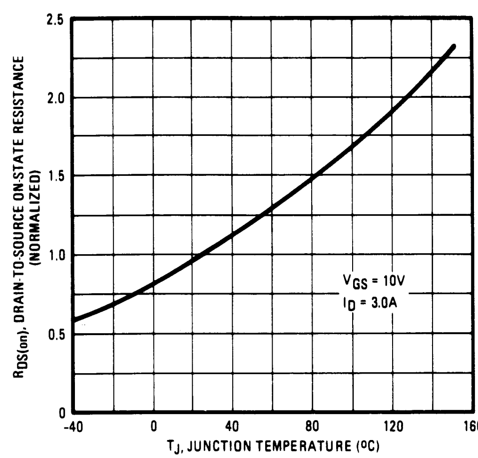


Fig. 9 — Normalized On-Resistance Vs. Temperature

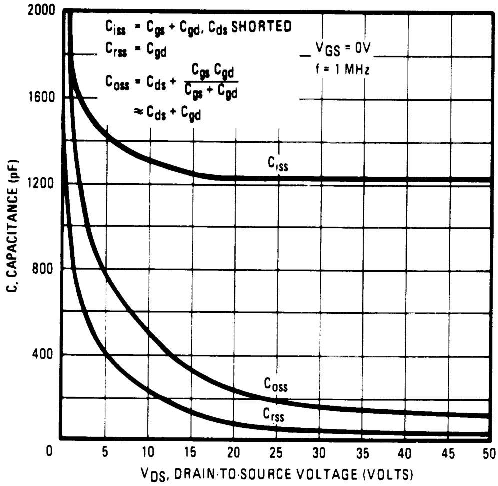


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

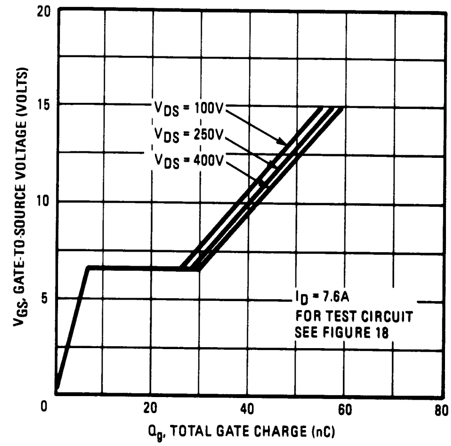


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

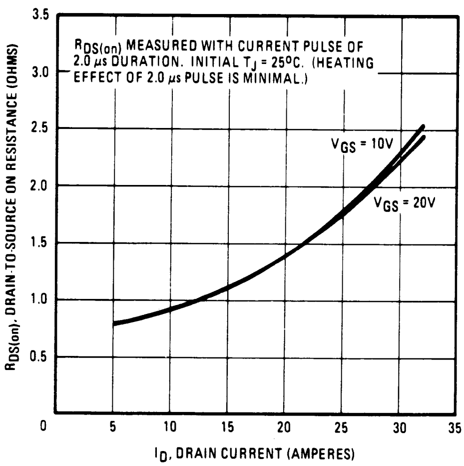


Fig. 12 — Typical On-Resistance Vs. Drain Current

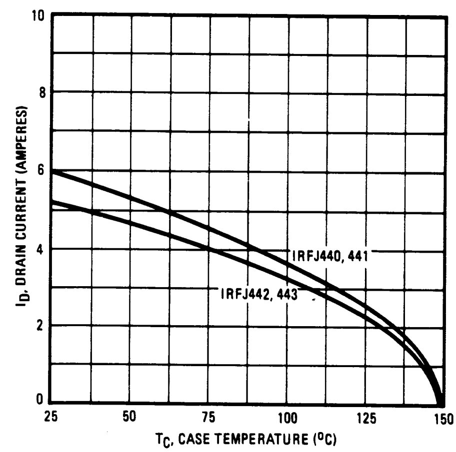


Fig. 13 — Maximum Drain Current Vs. Case Temperature

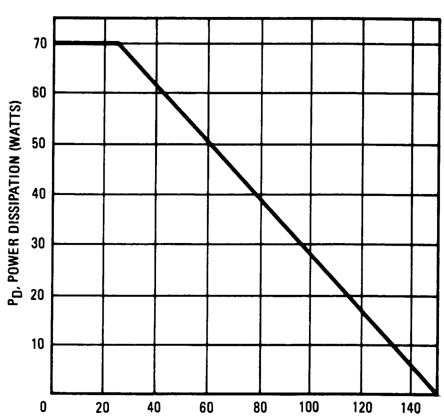


Fig. 14 — Power Vs. Temperature Derating Curve

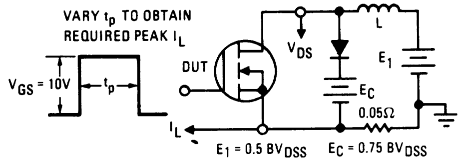


Fig. 15 — Clamped Inductive Test Circuit

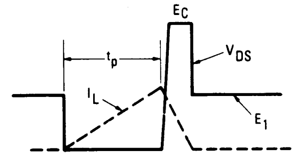


Fig. 16 — Clamped Inductive Waveforms

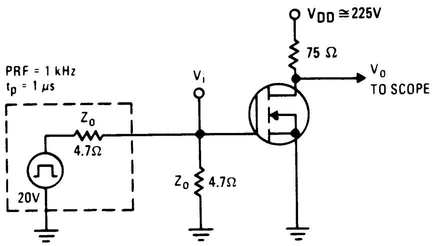


Fig. 17 — Switching Time Test Circuit

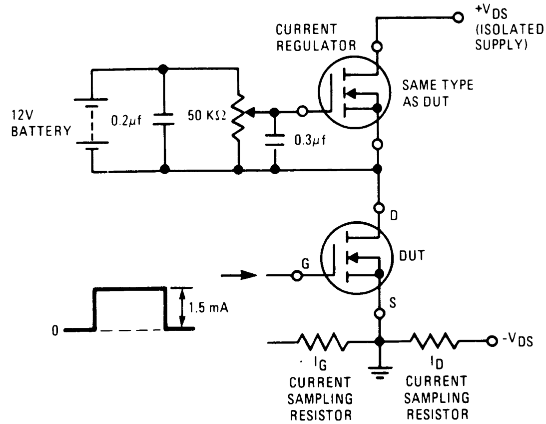


Fig. 18 — Gate Charge Test Circuit

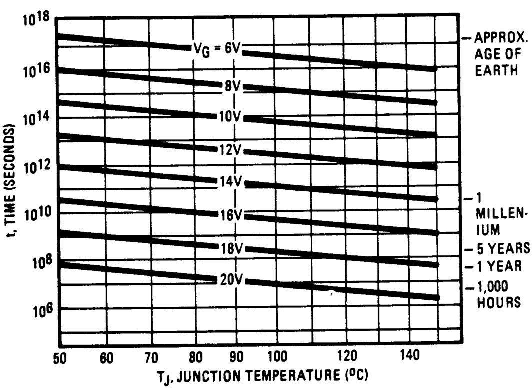


*Fig. 19 — Typical Time to Accumulated 1% Failure

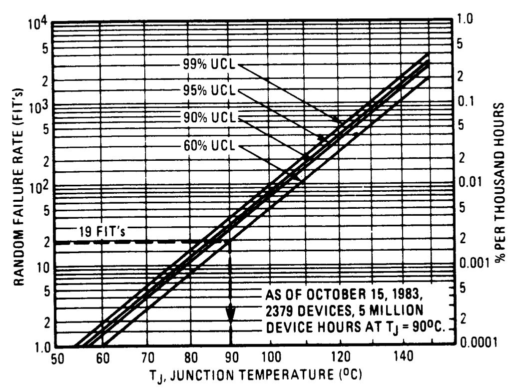


Fig. 20 — Typical High Temperature Reverse Bias (HTRB) Failure Rate

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